

N- and P-Channel 60V (D-S) Power MOSFET

FEATURES

- Low $R_{DS(on)}$ to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and R_g tested
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

APPLICATIONS

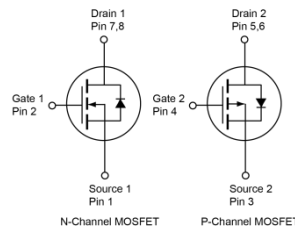
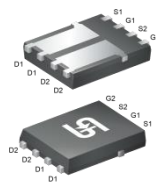
- DC-DC Converters
- Power Routing
- Motor Drives

KEY PERFORMANCE PARAMETERS

PARAMETER		TYPE	VALUE	UNIT
V_{DS}		N-ch	60	V
		P-ch	-60	
$R_{DS(on)}$ (max)	$V_{GS} = 10V$	N-ch	34	mΩ
	$V_{GS} = 4.5V$		40	
	$V_{GS} = -10V$	P-ch	68	
	$V_{GS} = -4.5V$		110	
Q_g		N-ch	10.3	nC
		P-ch	9.5	



PDFN56 Dual



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	N-ch	P-ch	UNIT
Drain-Source Voltage		V_{DS}	60	-60	V
Gate-Source Voltage		V_{GS}	± 20	± 20	V
Continuous Drain Current (Note 1)	$T_C = 25^\circ\text{C}$	I_D	24	-18	A
	$T_A = 25^\circ\text{C}$		5.4	-4	
Pulsed Drain Current		I_{DM}	96	-72	A
Single Pulse Avalanche Current (Note 2)		I_{AS}	12.7	-12.7	A
Single Pulse Avalanche Energy (Note 2)		E_{AS}	24	24	mJ
Total Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	40	40	W
	$T_C = 125^\circ\text{C}$		8.1	8.1	
Total Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	2	2	W
	$T_A = 125^\circ\text{C}$		0.4	0.4	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150		$^\circ\text{C}$

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Thermal Resistance – Junction to Case	$R_{\theta JC}$	3.1	$^\circ\text{C/W}$
Thermal Resistance – Junction to Ambient	$R_{\theta JA}$	61	

Thermal Performance Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)							
PARAMETER	CONDITIONS	SYMBOL	TYPE	MIN	TYP	MAX	UNIT
Static							
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	BV _{DSS}	N-ch	60	--	--	V
	V _{GS} = 0V, I _D = -250μA		P-ch	-60	--	--	
Gate Threshold Voltage	V _{GS} = V _{DS} , I _D = 250μA	V _{GS(TH)}	N-ch	1.2	1.7	2.5	V
	V _{GS} = V _{DS} , I _D = -250μA		P-ch	-1.2	-1.5	-2.5	
Gate-Source Leakage Current	V _{GS} = ±20V, V _{DS} = 0V	I _{GSS}	N-ch	--	--	±100	nA
	V _{GS} = ±20V, V _{DS} = 0V		P-ch	--	--	±100	nA
Drain-Source Leakage Current	V _{GS} = 0V, V _{DS} = 60V	I _{DSS}	N-ch	--	--	1	μA
	V _{GS} = 0V, V _{DS} = 60V T _J = 125°C			--	--	100	
	V _{GS} = 0V, V _{DS} = -60V		P-ch	--	--	-1	
	V _{GS} = 0V, V _{DS} = -60V T _J = 125°C			--	--	-100	
Drain-Source On-State Resistance ^(Note 3)	V _{GS} = 10V, I _D = 5.4A	R _{DS(on)}	N-ch	--	28	34	mΩ
	V _{GS} = 4.5V, I _D = 4.9A			--	33	40	
	V _{GS} = -10V, I _D = -4A		P-ch	--	57	68	
	V _{GS} = -4.5V, I _D = -3.2A			--	73	110	
Forward Transconductance ^(Note 3)	V _{DS} = 5V, I _D = 5.4A	g _{fs}	N-ch	--	19	--	S
	V _{DS} = -5V, I _D = -4A		P-ch	--	11	--	
Dynamic ^(Note 4)							
Total Gate Charge	N-ch V _{DS} = 30V, I _D = 5.4A P-ch V _{DS} = -30V, I _D = -4A	Q _{g(VGS=10V)}	N-ch	--	20.8	--	nC
		Q _{g(VGS=-10V)}	P-ch	--	18.1	--	
Total Gate Charge	N-ch V _{DS} = 30V, I _D = 4.9A P-ch V _{DS} = -30V, I _D = -3.2A	Q _{g(VGS=4.5V)}	N-ch	--	10.3	--	
		Q _{g(VGS=-4.5V)}	P-ch	--	9.5	--	
Gate-Source Charge		Q _{gs}	N-ch	--	3.9	--	
			P-ch	--	2.6	--	
Gate-Drain Charge		Q _{gd}	N-ch	--	4.2	--	
			P-ch	--	4.8	--	
Input Capacitance	N-ch V _{GS} = 0V, V _{DS} = 30V f = 1.0MHz P-ch	C _{iss}	N-ch	--	1159	--	pF
			P-ch	--	930	--	
Output Capacitance		C _{oss}	N-ch	--	59	--	
			P-ch	--	65	--	
Reverse Transfer Capacitance	V _{GS} = 0V, V _{DS} = -30V f = 1.0MHz	C _{rss}	N-ch	--	15	--	
			P-ch	--	26	--	
Gate Resistance	f = 1.0MHz	R _g	N-ch	0.6	2	4	Ω
			P-ch	4.5	15	30	

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)							
PARAMETER	CONDITIONS	SYMBOL	TYPE	MIN	TYP	MAX	UNIT
Switching ^(Note 4)							
Turn-On Delay Time	N-ch V _{GS} = 10V, V _{DS} = 30V, I _D = 5.4A, R _G = 2Ω P-ch V _{GS} = -10V, V _{DS} = -30V, I _D = -4A, R _G = 2Ω	t _{d(on)}	N-ch	--	7.4	--	ns
			P-ch	--	4	--	
Turn-On Rise Time		t _r	N-ch	--	25	--	
			P-ch	--	28	--	
Turn-Off Delay Time		t _{d(off)}	N-ch	--	18	--	
			P-ch	--	44	--	
Turn-Off Fall Time		t _f	N-ch	--	18	--	
			P-ch	--	44	--	
Source-Drain Diode							
Forward Voltage ^(Note 3)	V _{GS} = 0V, I _S = 5.4A	V _{SD}	N-ch	--	--	1	V
	V _{GS} = 0V, I _S = -4A		P-ch	--	--	-1	
Reverse Recovery Time	N-ch I _S = 5.4A, dI/dt = 100A/μs P-ch I _S = -4A, dI/dt = 100A/μs	t _{rr}	N-ch	--	16	--	ns
			P-ch	--	13	--	
Reverse Recovery Charge		Q _{rr}	N-ch	--	11	--	nC
			P-ch	--	7.8	--	

Notes:

- Silicon limited current only.
- N-ch : $L = 0.3\text{mH}, V_{GS} = 10\text{V}, V_{DD} = 25\text{V}, R_G = 25\Omega, I_{AS} = 12.7\text{A}$, Starting $T_J = 25^\circ\text{C}$
P-ch : $L = 0.3\text{mH}, V_{GS} = -10\text{V}, V_{DD} = -25\text{V}, R_G = 25\Omega, I_{AS} = -12.7\text{A}$, Starting $T_J = 25^\circ\text{C}$
- Pulse test: Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- Switching time is essentially independent of operating temperature.

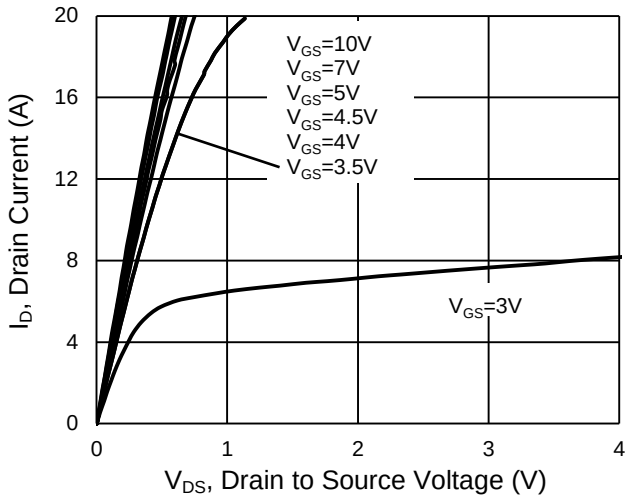
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM6502CR RLG	PDFN56 Dual	2,500pcs / 13" Reel

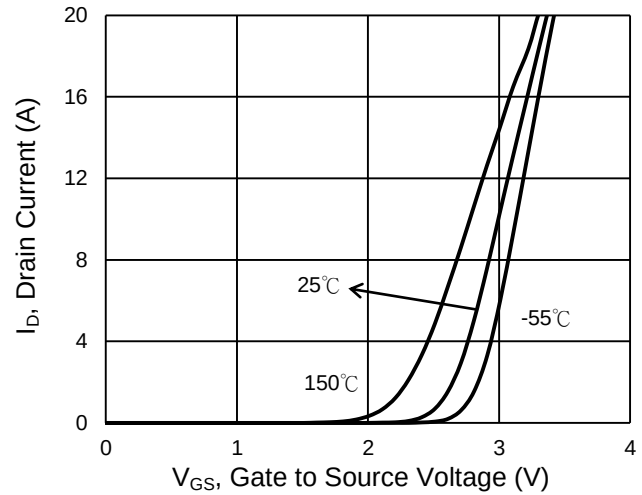
CHARACTERISTICS CURVES (N-Channel)

($T_A = 25^\circ\text{C}$ unless otherwise noted)

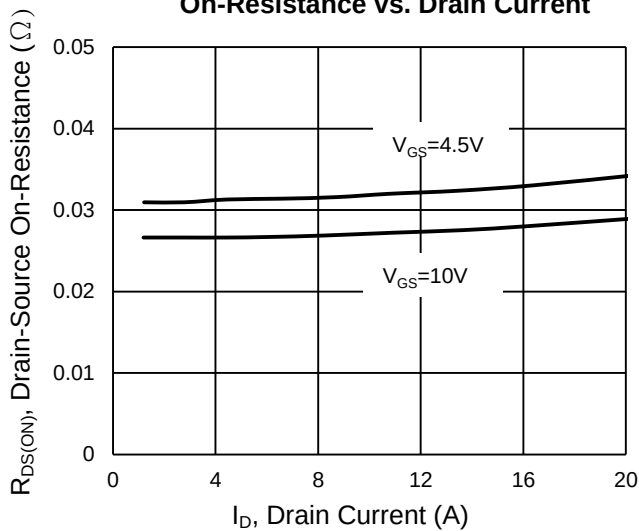
Output Characteristics



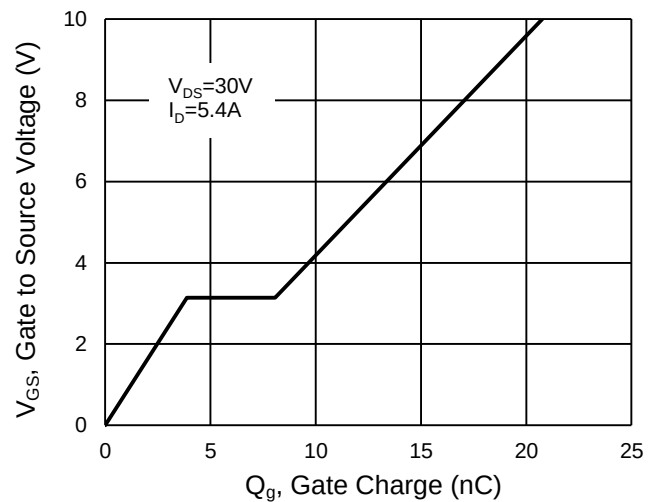
Transfer Characteristics



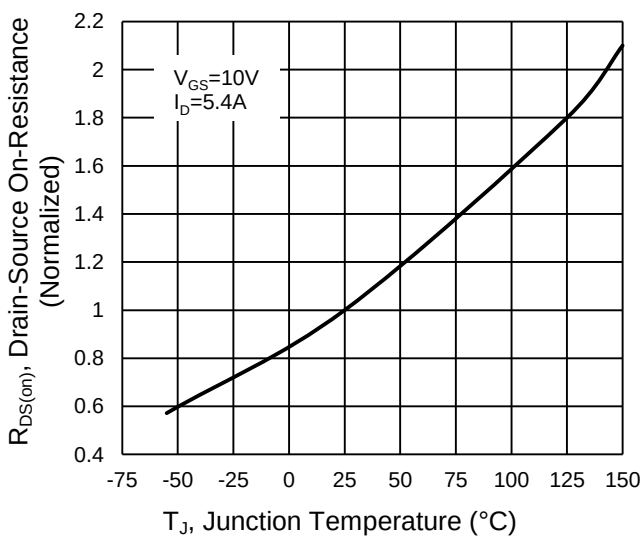
On-Resistance vs. Drain Current



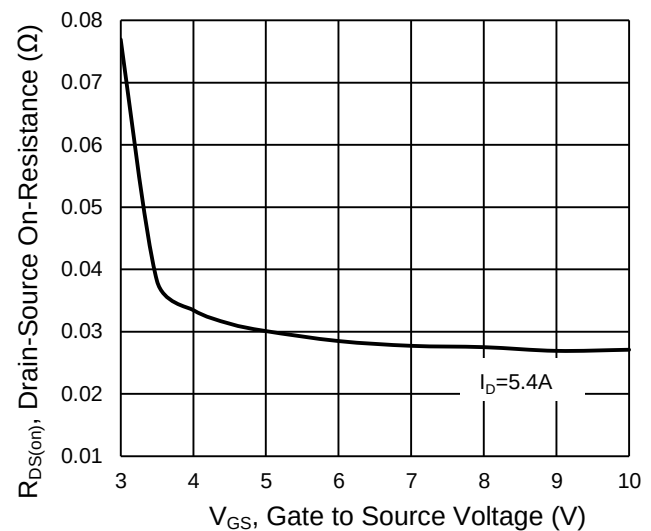
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



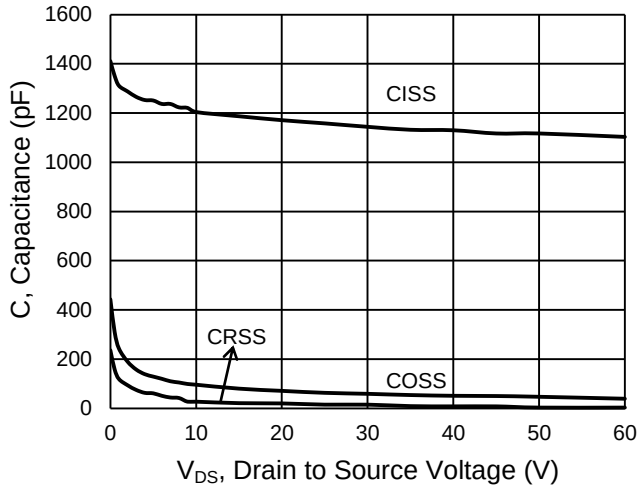
On-Resistance vs. Gate-Source Voltage



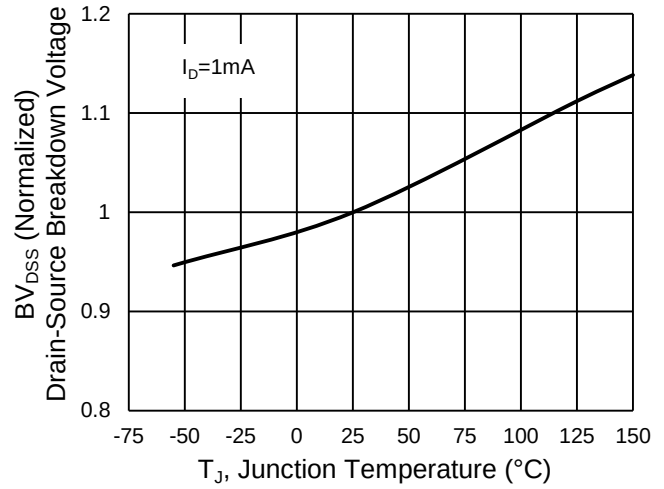
CHARACTERISTICS CURVES (N-Channel)

($T_A = 25^\circ\text{C}$ unless otherwise noted)

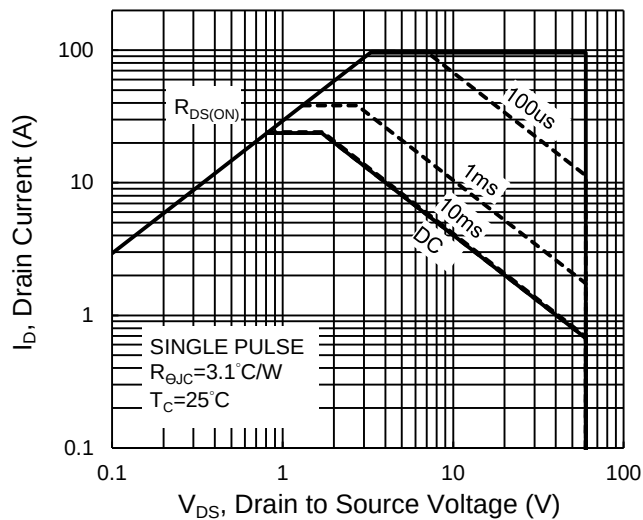
Capacitance vs. Drain-Source Voltage



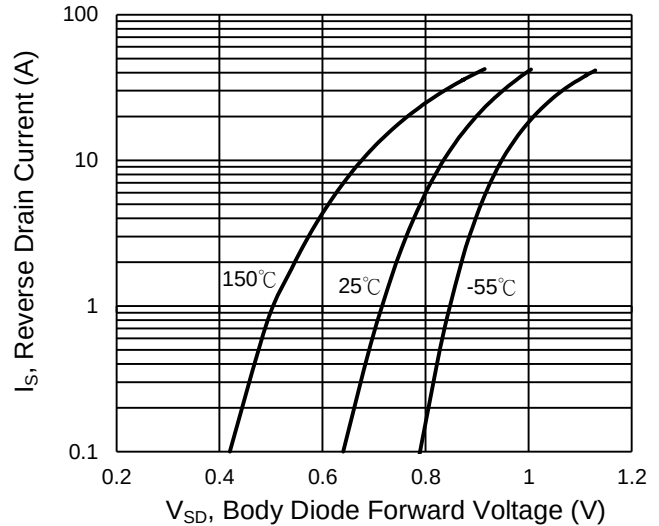
BV_{DSS} vs. Junction Temperature



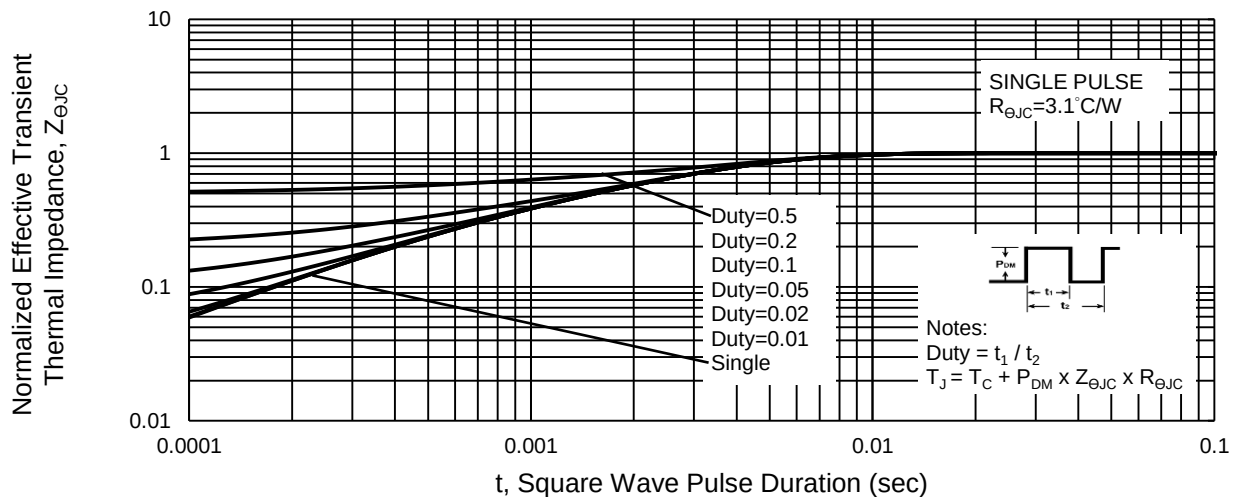
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage



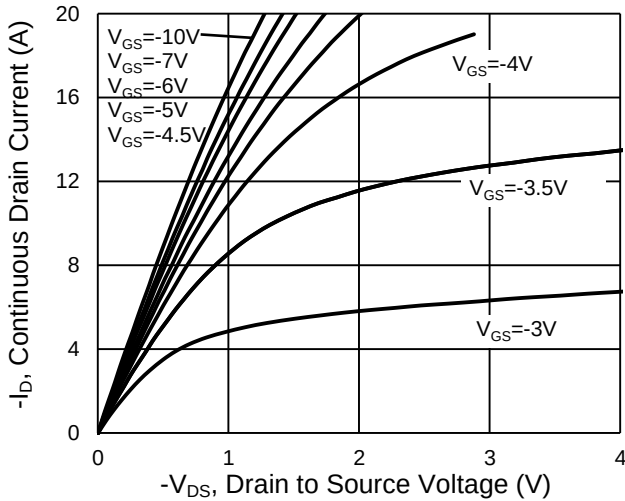
Normalized Thermal Transient Impedance, Junction-to-Case



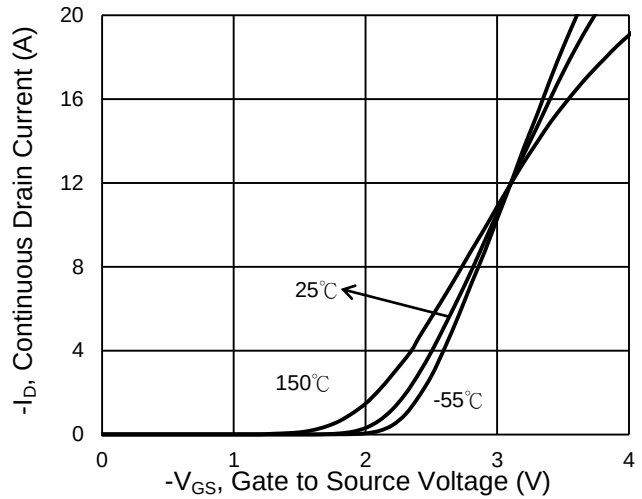
CHARACTERISTICS CURVES (P-Channel)

($T_A = 25^\circ\text{C}$ unless otherwise noted)

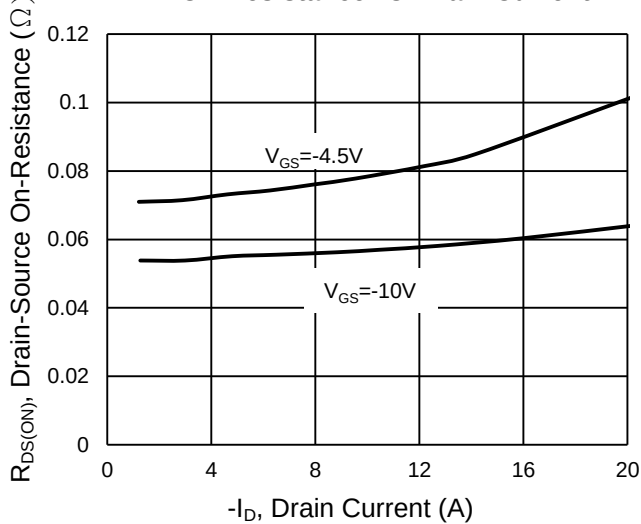
Output Characteristics



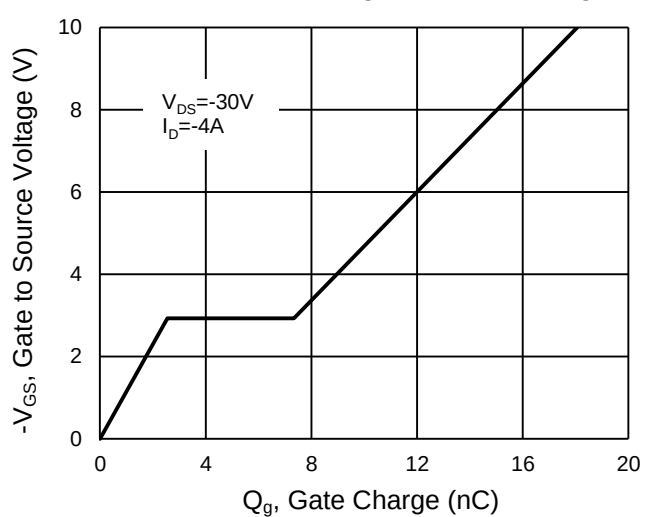
Transfer Characteristics



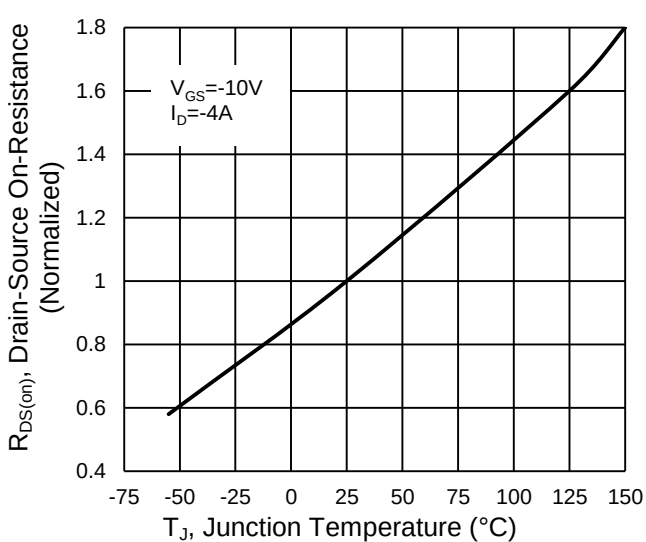
On-Resistance vs. Drain Current



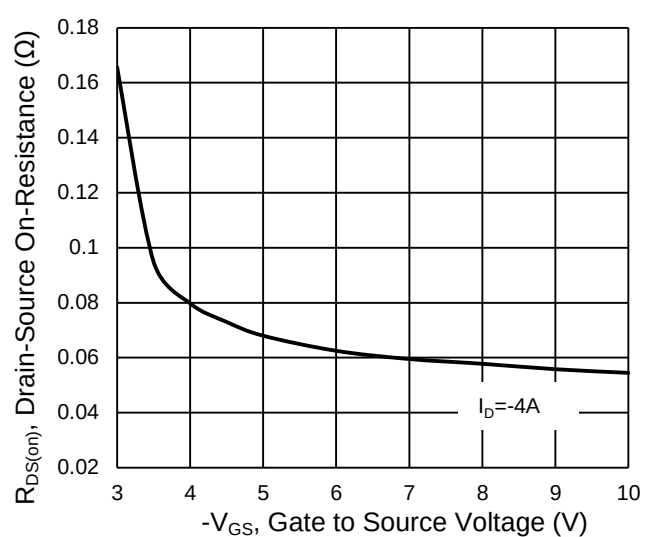
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



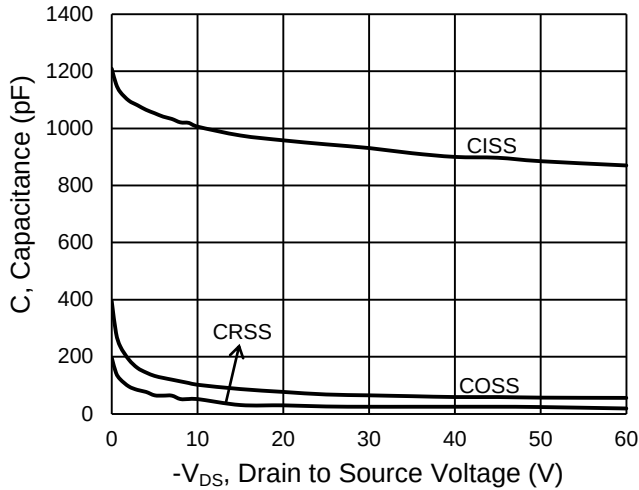
On-Resistance vs. Gate-Source Voltage



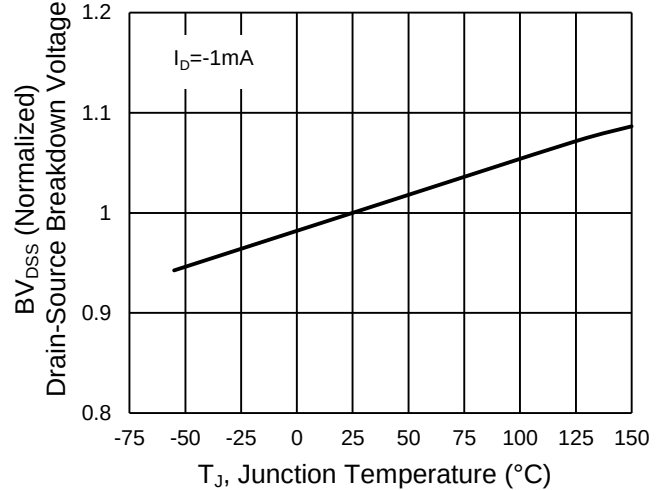
CHARACTERISTICS CURVES (P-Channel)

($T_A = 25^\circ\text{C}$ unless otherwise noted)

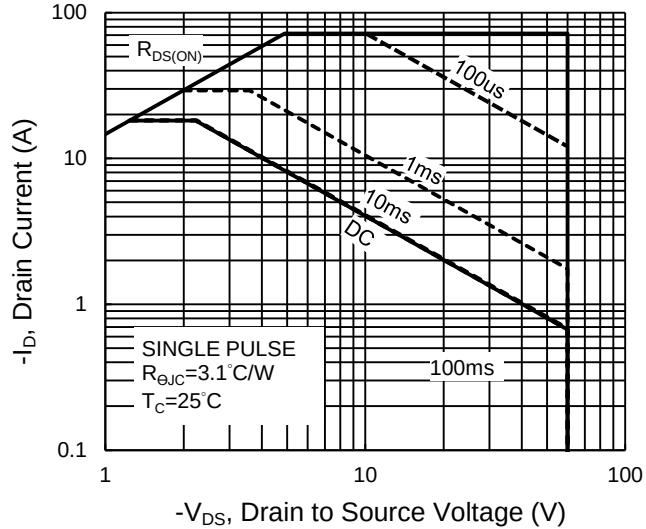
Capacitance vs. Drain-Source Voltage



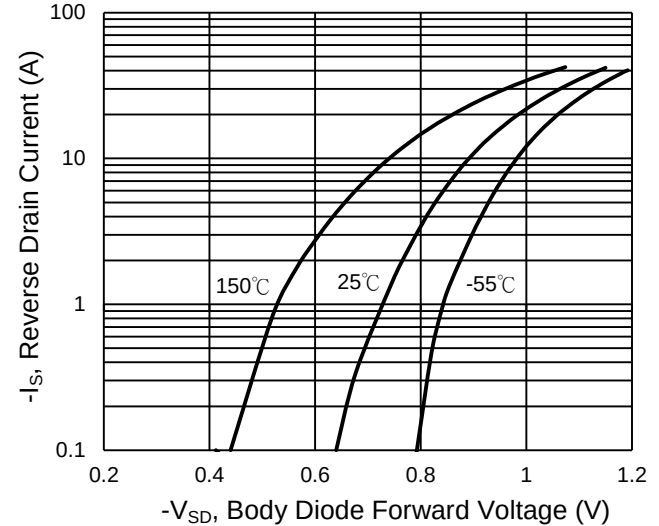
BV_{DSS} vs. Junction Temperature



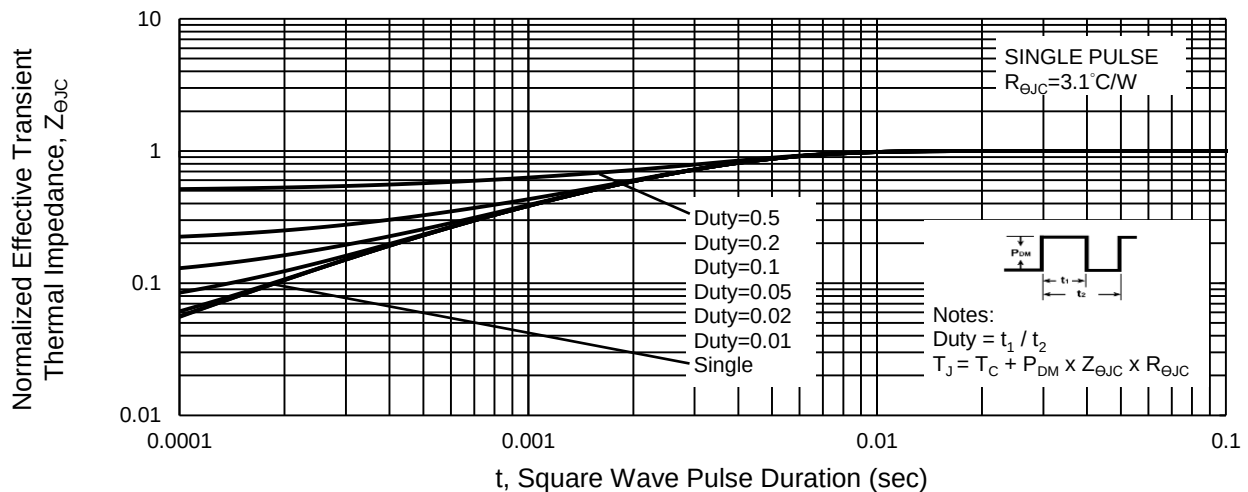
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage



Normalized Thermal Transient Impedance, Junction-to-Case



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